

Features

- Low forward voltage drop
- High reverse voltage
- Hermetic metal cases with ceramic insulators

Typical Applications

- All purpose high power rectifier diodes
- High power resistance welding equipment
- Non-controllable and half-controllable

$I_{F(AV)}$ **400A**
 V_{RRM} **1100~2000 V**
 I_{FSM} **10 kA**
 I^2t **500 10³A²S**



SYMBOL	CHARACTERISTIC	TEST CONDITIONS		T _j (°C)	VALUE			UNIT
					Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Double side cooled,	T _c =85°C	175			1080	A
V_{RRM}	Repetitive peak reverse voltage	tp=10ms		175	1100		2000	V
I_{RRM}	Repetitive peak current	at V _{RRM}		175			30	mA
I_{FSM}	Surge forward current	10ms half sine wave		175			10	kA
I^2t	I ² t for fusing coordination	V _R =0.6V _{RRM}					500	A ² s*10 ³
V_{FO}	Threshold voltage			175			0.98	V
r_F	Forward slope resistance						0.33	mΩ
V_{FM}	Peak forward voltage	I _{FM} =1200A, F=7.0kN		25			1.80	V
Q_{rr}	Recovery charge	I _{FM} =2000A, tp=2000μs, di/dt=-20A/μs, V _R =50V		175		1600		μC
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180° sine: double side cooled Clamping force 7.0kN					0.045	°C /W
$R_{th(c-h)}$	Thermal resistance case to heat sink					0.010		
F_m	Mounting force				5.3		10	kN
T_{stg}	Stored temperature				-40		175	°C
W_t	Weight					80		g
Outline	ZT25aT							

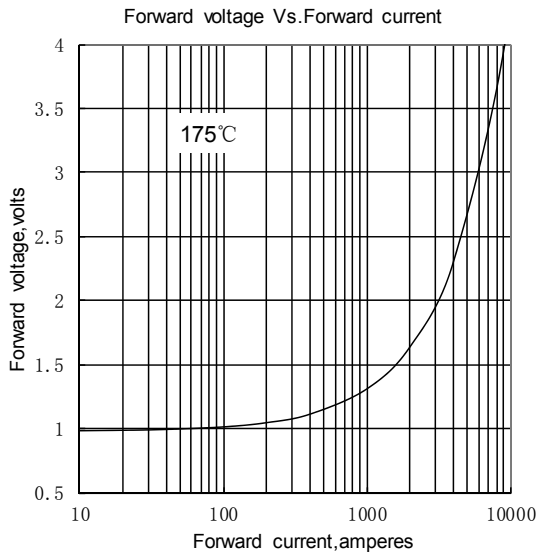


Fig.1

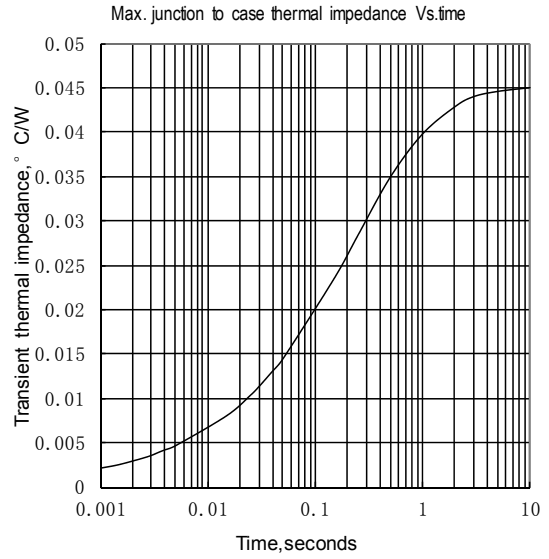


Fig.2

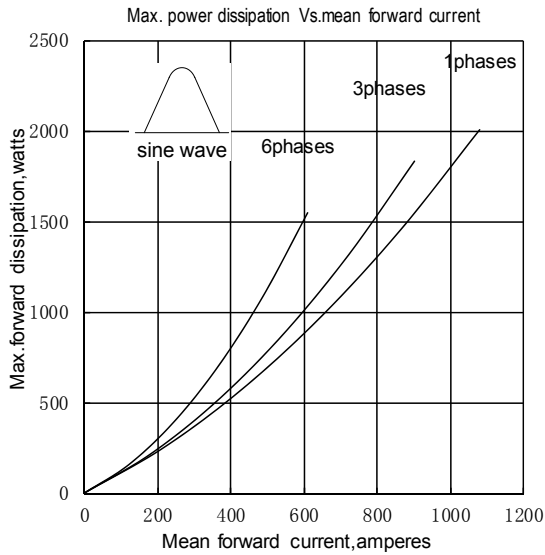


Fig.3

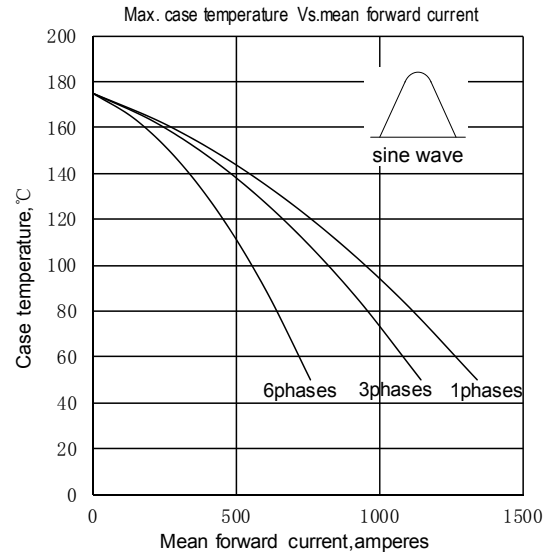


Fig.4

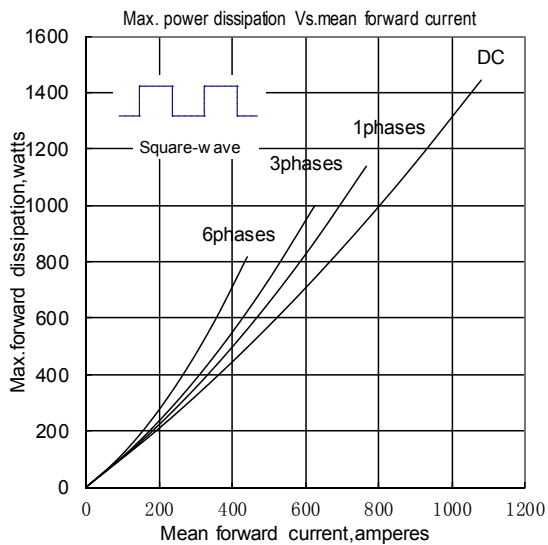


Fig.5

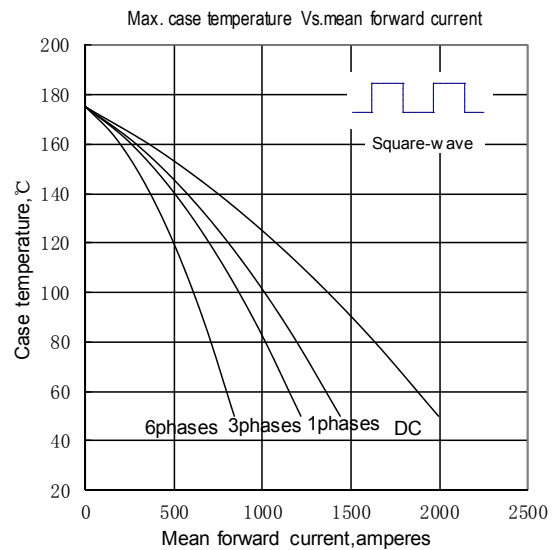


Fig.6

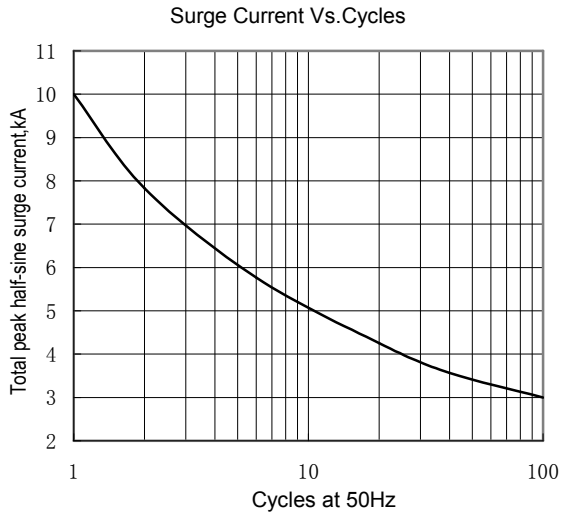


Fig.7

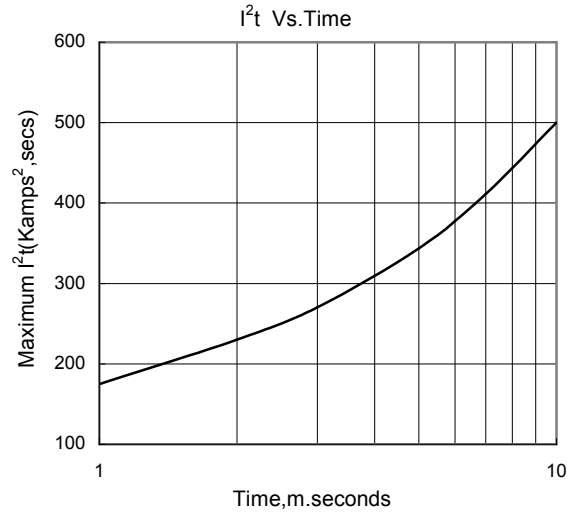


Fig.8

Outline:

